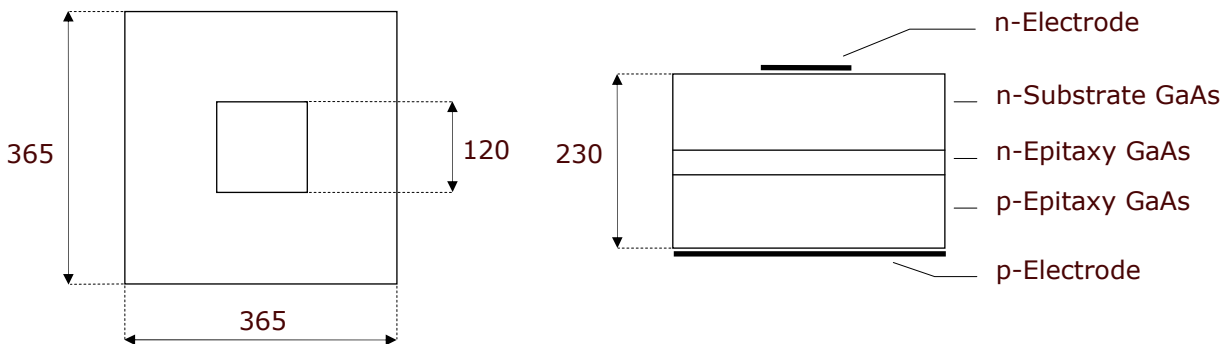


INFRA-RED

Item No.: 120124

1. This specification applies to GaAs / GaAs LED Chips
2. Structure
 - 2.1 Mesa structure
 - 2.2 Electrodes

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire bond contacts can also have a spider shape

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	V_F	$I_F = 20 \text{ mA}$		1,20	1,40	V
Reverse current	I_R	$V_R = 5 \text{ V}$			10	μA
output Power *	Φ_e	$I_F = 20 \text{ mA}$	0,9	1,0		mW
		$I_F = 50 \text{ mA}$	2,3	2,5		
Switching time	t_r, t_f	$I_F = 100 \text{ mA}$		0,6		μs
Peak wavelength	λ_p	$I_F = 20 \text{ mA}$		930		nm

* On request, wafers will be delivered according to output power classes
Power measurement at OSA on gold plate

5. Packing
 - 1) wire bond side on top
 - 2) back contact on top

6. Labeling

Type	Lot No.	Φ_e typ min max	Quantity
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